

No.5031

2SA1965

PNP Epitaxial Planar Silicon Transistor

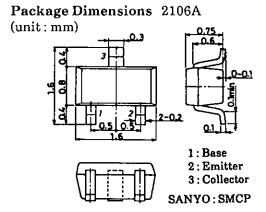
Muting Circuit Applications

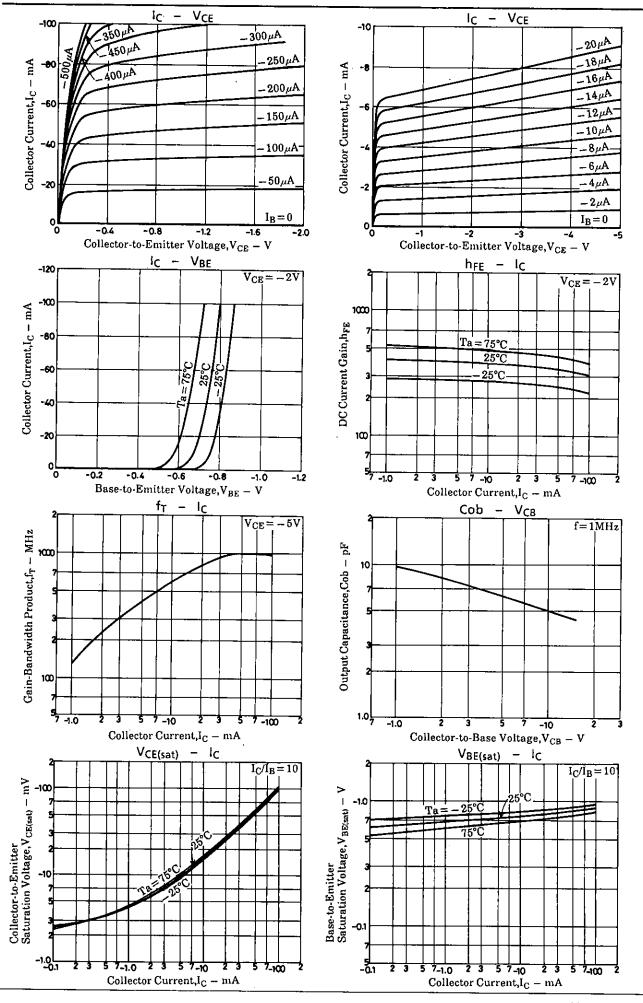
Features

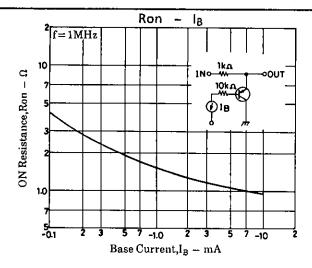
- · Very small-sized package permitting 2SA1965-applied sets to be made small and slim.
- · Small output capacitance.
- · Low collector-to-emitter saturation voltage.
- · Small ON resistance.

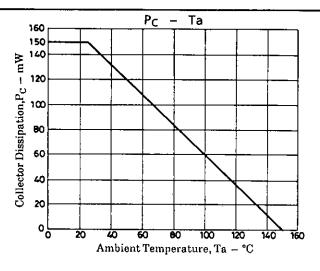
Absolute Maximum Ratings at Ta = 25°C					unit	
Collector-to-Base Voltage	V_{CBO}		_	- 15	V	
Collector-to-Emitter Voltage	V_{CEO}	•	-	-10	V	
Emitter-to-Base Voltage	V_{EBO}			-5	V	
Collector Current	I_{C}		_	100	mΑ	
Collector Current (Pulse)	I_{CP}			200	mΑ	
Base Current	IB			- 2 0	mA	
Collector Dissipation	$P_{\mathbf{C}}$			150	mW	
Junction Temperature	Тj			150	°C	
Storage Temperature	Tstg		-55 to +		°Č	
Electrical Characteristics at Ta = 25°C			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -12V, I_E = 0$		• •	-0.1	μ A
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4V, I_{C} = 0$			-0.1	μ A
DC Current Gain		$V_{CE} = -2V, I_C = -5mA$	200		600	,
Gain-Bandwidth Product		$V_{CE} = -5V_{IC} = -10 \text{mA}$		600		MHz
Output Capacitance	Cob	$V_{CB} = -10V, f = 1MHz$		5.0		рF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_{C} = -10 \text{mA}, I_{B} = -1 \text{mA}$		-16	-35	mV
B-E Saturation Voltage	,,	$I_{C} = -10 \text{mA}, I_{B} = -1 \text{mA}$	_	0.75	-1.1	V
C-B Breakdown Voltage		$I_{\rm C} = -10 \mu A, I_{\rm E} = 0$	-15			V
C-E Breakdown Voltage	1211,020	$I_C = -1 \text{mA}, R_{BE} = \infty$	-10			V
E-B Breakdown Voltage	V	$I_{\rm E} = -10 \mu A, I_{\rm C} = 0$	-5			V
ON Resistance		$I_B = -3 \text{mA}, f = 1 \text{MHz}$	-	1.2		Ω

Marking: KA









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